

[illegible]

A cross-sectional view of a semiconductor device 100. The device is shown between two vertical planes, H and H'. It consists of a substrate 10 with a top layer 20. A central region 50 is defined by two vertical boundaries 30. A layer 52 is located between the top layer 20 and the substrate 10. A layer 21 is on top of the central region 50. A layer 23 is on top of the layer 21. A layer 53 is on top of the layer 23. A layer 202 is on the left side of the device, and a layer 201 is on the right side. A layer 52 is also shown on the right side of the device. A layer 205 is on the bottom right side of the device.

FIG. 3

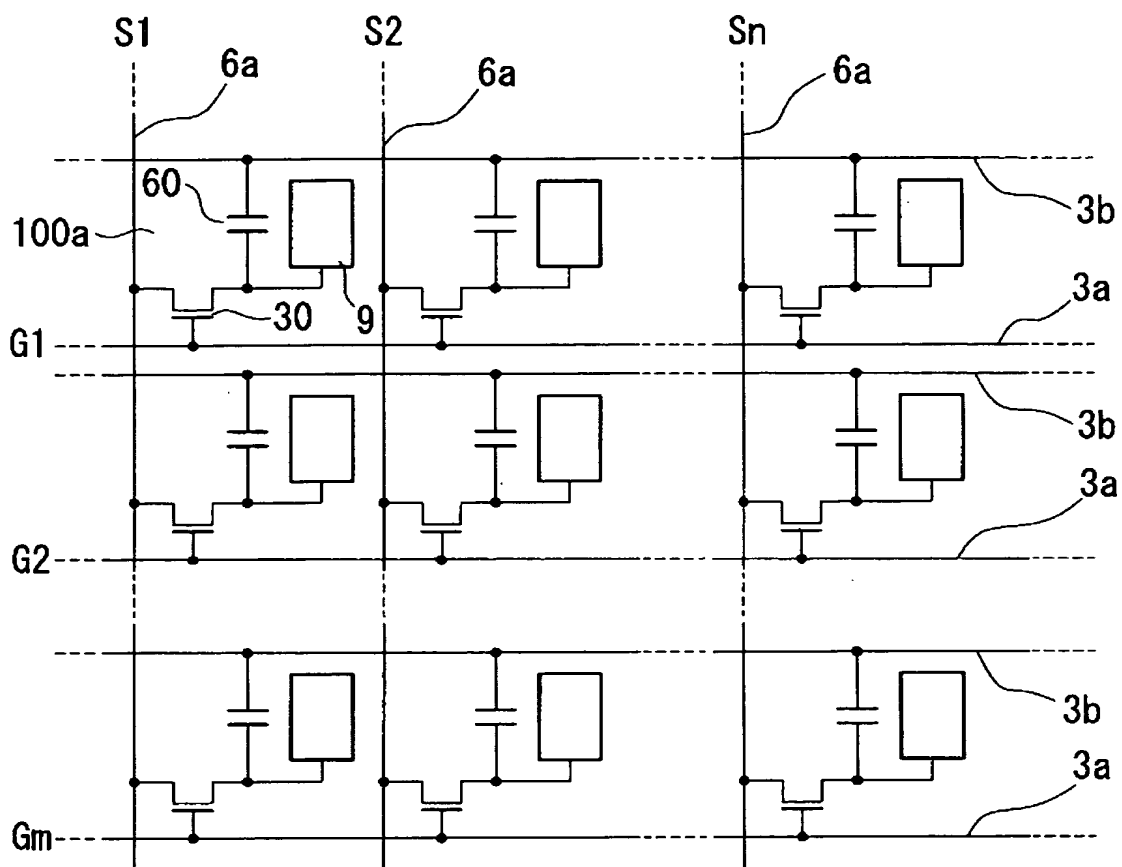


FIG. 4

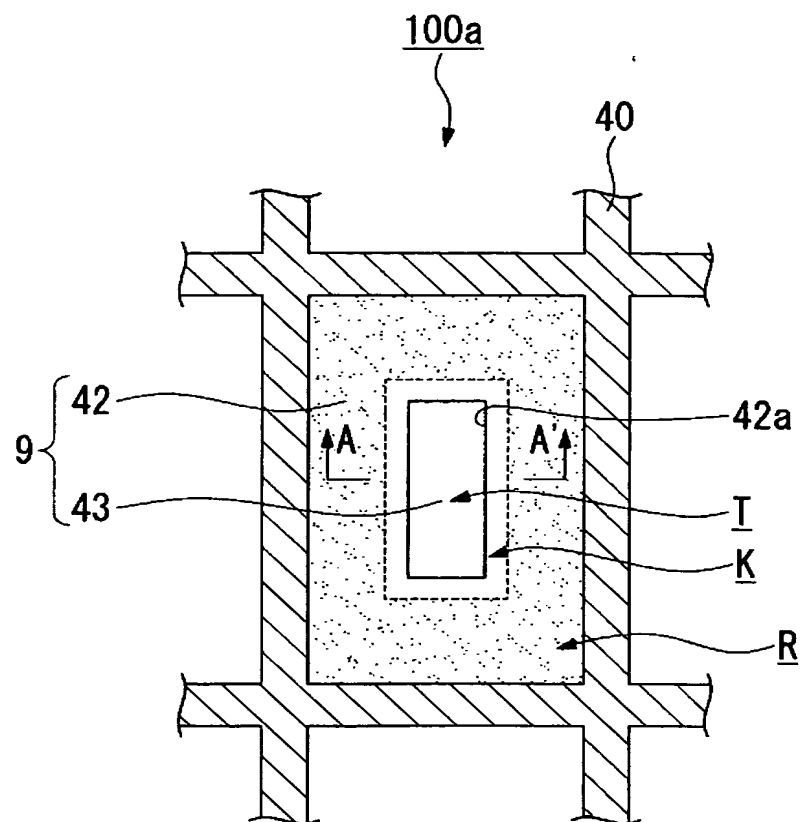


FIG. 5

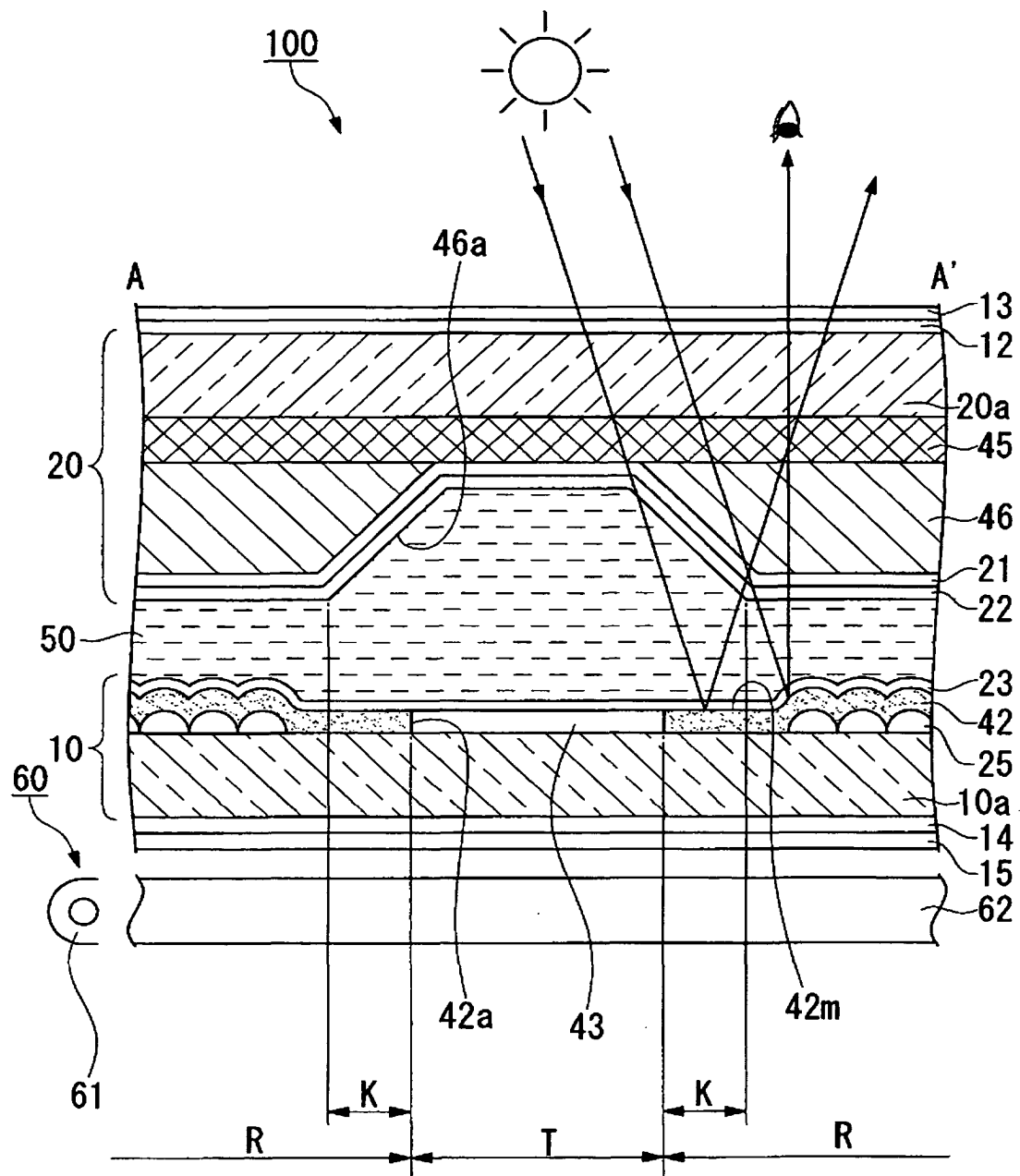


FIG. 6

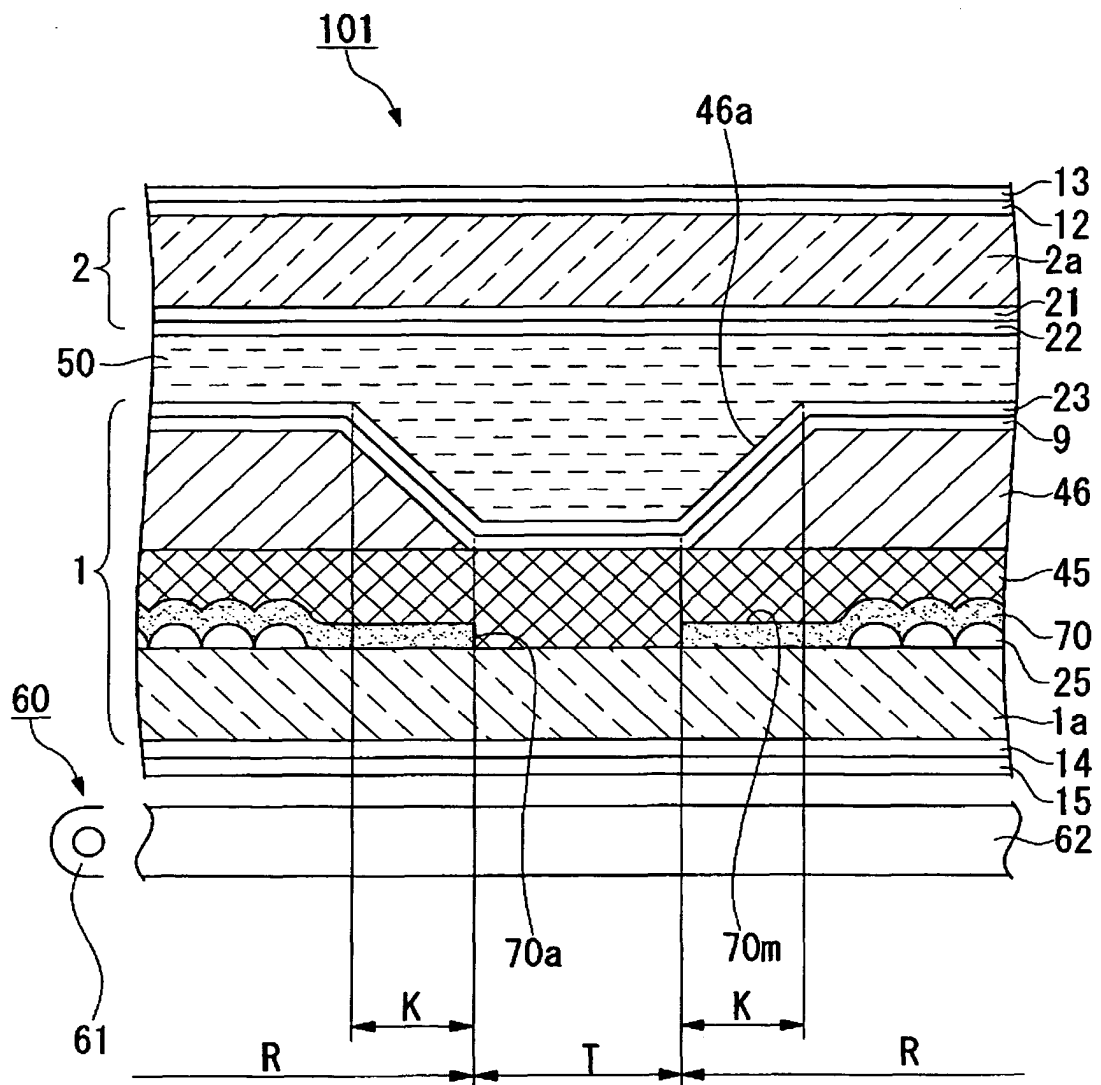


FIG. 7

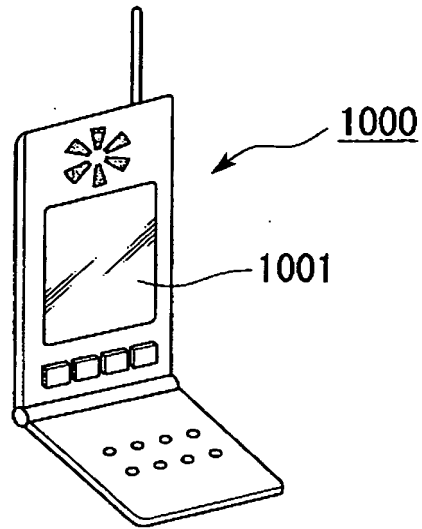


FIG. 8

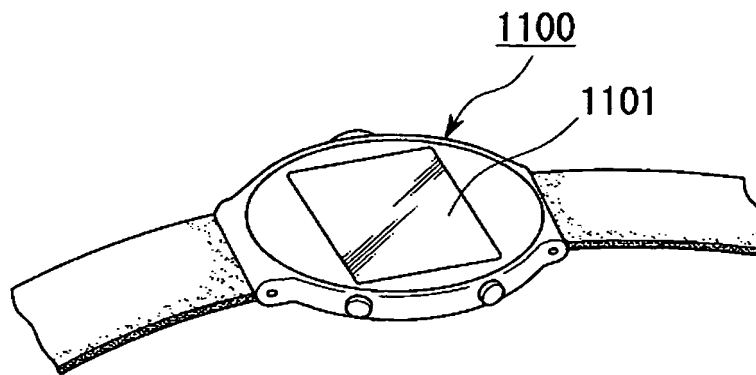


FIG. 9

